

Kah-Wee Ang

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

139 papers	3,249 citations	32 h-index	51 g-index
154 ext. papers	4,155 ext. citations	7.4 avg, IF	5.59 L-index

#	Paper	IF	Citations
139	Silicon Modulators and Germanium Photodetectors on SOI: Monolithic Integration, Compatibility, and Performance Optimization. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2010 , 16, 307-315	3.8	179
138	Artificial Synapses Based on Multiterminal Memtransistors for Neuromorphic Application. <i>Advanced Functional Materials</i> , 2019 , 29, 1901106	15.6	121
137	Al-Doped Black Phosphorus pB Homojunction Diode for High Performance Photovoltaic. <i>Advanced Functional Materials</i> , 2017 , 27, 1604638	15.6	120
136	Monolithic Polarization and Phase Diversity Coherent Receiver in Silicon. <i>Journal of Lightwave Technology</i> , 2010 , 28, 520-525	4	109
135	WDM multi-channel silicon photonic receiver with 320 Gbps data transmission capability. <i>Optics Express</i> , 2010 , 18, 5106-13	3.3	102
134	Waveguide-Integrated Black Phosphorus Photodetector for Mid-Infrared Applications. <i>ACS Nano</i> , 2019 , 13, 913-921	16.7	96
133	Few-Layer Black Phosphorus Carbide Field-Effect Transistor via Carbon Doping. <i>Advanced Materials</i> , 2017 , 29, 1700503	24	95
132	Lattice strain analysis of transistor structures with silicon-germanium and silicon-carbon source-drain stressors. <i>Applied Physics Letters</i> , 2005 , 86, 093102	3.4	89
131	2D Photovoltaic Devices: Progress and Prospects. <i>Small Methods</i> , 2018 , 2, 1700294	12.8	77
130	A Black Phosphorus Carbide Infrared Phototransistor. <i>Advanced Materials</i> , 2018 , 30, 1705039	24	75
129	A Fully Printed Flexible MoS ₂ Memristive Artificial Synapse with Femtojoule Switching Energy. <i>Advanced Electronic Materials</i> , 2019 , 5, 1900740	6.4	71
128	Direct n- to p-Type Channel Conversion in Monolayer/Few-Layer WS Field-Effect Transistors by Atomic Nitrogen Treatment. <i>ACS Nano</i> , 2018 , 12, 2506-2513	16.7	67
127	Wearable Triboelectric-Human-Machine Interface (THMI) Using Robust Nanophotonic Readout. <i>ACS Nano</i> , 2020 , 14, 8915-8930	16.7	63
126	Impact and Origin of Interface States in MOS Capacitor with Monolayer MoS and HfO High-k Dielectric. <i>Scientific Reports</i> , 2017 , 7, 40669	4.9	61
125	Split Bullseye shaped aluminum antenna for plasmon-enhanced nanometer scale germanium photodetector. <i>Nano Letters</i> , 2011 , 11, 1289-93	11.5	60
124	Infrared Black Phosphorus Phototransistor with Tunable Responsivity and Low Noise Equivalent Power. <i>ACS Applied Materials & Interfaces</i> , 2017 , 9, 36130-36136	9.5	57
123	Black Phosphorus N-Type Field-Effect Transistor with Ultrahigh Electron Mobility via Aluminum Adatoms Doping. <i>Small</i> , 2017 , 13, 1602909	11	56

122	High Mobility Anisotropic Black Phosphorus Nanoribbon Field-Effect Transistor. <i>Advanced Functional Materials</i> , 2018 , 28, 1801524	15.6	53
121	All-Dielectric Surface-Enhanced Infrared Absorption-Based Gas Sensor Using Guided Resonance. <i>ACS Applied Materials & Interfaces</i> , 2018 , 10, 38272-38279	9.5	52
120	Monolithically Integrated Flexible Black Phosphorus Complementary Inverter Circuits. <i>ACS Nano</i> , 2017 , 11, 7416-7423	16.7	43
119	n-MOSFET With Silicon-Carbon Source/Drain for Enhancement of Carrier Transport. <i>IEEE Transactions on Electron Devices</i> , 2007 , 54, 249-256	2.9	43
118	A van der Waals Synaptic Transistor Based on Ferroelectric Hf _{0.5} Zr _{0.5} O ₂ and 2D Tungsten Disulfide. <i>Advanced Electronic Materials</i> , 2020 , 6, 2000057	6.4	41
117	Nickel-Silicide/Carbon Contact Technology for N-Channel MOSFETs With Silicon-Carbon Source/Drain. <i>IEEE Electron Device Letters</i> , 2008 , 29, 89-92	4.4	41
116	Black Phosphorus Carbide as a Tunable Anisotropic Plasmonic Metasurface. <i>ACS Photonics</i> , 2018 , 5, 3116-3123	6.3	39
115	Electronic Devices and Circuits Based on Wafer-Scale Polycrystalline Monolayer MoS ₂ by Chemical Vapor Deposition. <i>Advanced Electronic Materials</i> , 2019 , 5, 1900393	6.4	38
114	Novel Silicon-Carbon (Si:C) Schottky Barrier Enhancement Layer for Dark-Current Suppression in Ge-on-SOI MSM Photodetectors. <i>IEEE Electron Device Letters</i> , 2008 , 29, 704-707	4.4	38
113	Zero-bias mid-infrared graphene photodetectors with bulk photoresponse and calibration-free polarization detection. <i>Nature Communications</i> , 2020 , 11, 6404	17.4	37
112	Low Thermal Budget Monolithic Integration of Evanescent-Coupled Ge-on-SOI Photodetector on Si CMOS Platform. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2010 , 16, 106-113	3.8	36
111	Monolayer WxMo _{1-x} S ₂ Grown by Atmospheric Pressure Chemical Vapor Deposition: Bandgap Engineering and Field Effect Transistors. <i>Advanced Functional Materials</i> , 2017 , 27, 1606469	15.6	34
110	Anomalous resistive switching in memristors based on two-dimensional palladium diselenide using heterophase grain boundaries. <i>Nature Electronics</i> , 2021 , 4, 348-356	28.4	34
109	Surface plasmon enhanced responsivity in a waveguided germanium metal-semiconductor-metal photodetector. <i>Applied Physics Letters</i> , 2010 , 97, 091102	3.4	33
108	2D photonic memristor beyond graphene: progress and prospects. <i>Nanophotonics</i> , 2020 , 9, 1579-1599	6.3	32
107	Black Phosphorus Based Field Effect Transistors with Simultaneously Achieved Near Ideal Subthreshold Swing and High Hole Mobility at Room Temperature. <i>Scientific Reports</i> , 2016 , 6, 24920	4.9	31
106	Impact of field-enhanced band-traps-band tunneling on the dark current generation in germanium p-i-n photodetector. <i>Applied Physics Letters</i> , 2009 , 94, 223515	3.4	30
105	Low-Voltage and High-Responsivity Germanium Bipolar Phototransistor for Optical Detections in the Near-Infrared Regime. <i>IEEE Electron Device Letters</i> , 2008 , 29, 1124-1127	4.4	30

104	Black Phosphorus Transistors with Near Band Edge Contact Schottky Barrier. <i>Scientific Reports</i> , 2015 , 5, 18000	4.9	29
103	High-Performance Waveguided Ge-on-SOI Metal-Semiconductor-Metal Photodetectors With Novel Silicon-Carbon (Si : C) Schottky Barrier Enhancement Layer. <i>IEEE Photonics Technology Letters</i> , 2008 , 20, 754-756	2.2	28
102	High-Responsivity Mid-Infrared Black Phosphorus Slow Light Waveguide Photodetector. <i>Advanced Optical Materials</i> , 2020 , 8, 2000337	8.1	27
101	Germanium-on-SOI waveguides for mid-infrared wavelengths. <i>Optics Express</i> , 2016 , 24, 11987-93	3.3	27
100	Efficient and reliable surface charge transfer doping of black phosphorus via atomic layer deposited MgO toward high performance complementary circuits. <i>Nanoscale</i> , 2018 , 10, 17007-17014	7.7	27
99	Strained n-Channel Transistors With Silicon Source and Drain Regions and Embedded Silicon/Germanium as Strain-Transfer Structure. <i>IEEE Electron Device Letters</i> , 2007 , 28, 609-612	4.4	27
98	Wafer-Scale 2D Hafnium Diselenide Based Memristor Crossbar Array for Energy-Efficient Neural Network Hardware. <i>Advanced Materials</i> , 2021 , e2103376	24	27
97	Interface Engineering for the Enhancement of Carrier Transport in Black Phosphorus Transistor with Ultra-Thin High-k Gate Dielectric. <i>Scientific Reports</i> , 2016 , 6, 26609	4.9	26
96	Anomalous Broadband Spectrum Photodetection in 2D Rhenium Disulfide Transistor. <i>Advanced Optical Materials</i> , 2019 , 7, 1901115	8.1	26
95	Performance Enhancement in Uniaxial Strained Silicon-on-Insulator N-MOSFETs Featuring Silicon-Carbon Source/Drain Regions. <i>IEEE Transactions on Electron Devices</i> , 2007 , 54, 2910-2917	2.9	25
94	Dispersion engineering and thermo-optic tuning in mid-infrared photonic crystal slow light waveguides on silicon-on-insulator. <i>Optics Letters</i> , 2018 , 43, 5504-5507	3	25
93	Aluminum nitride on insulator (ALNOI) platform for mid-infrared photonics. <i>Optics Letters</i> , 2019 , 44, 73-75	7.5	25
92	Monolithic integration of MoS ₂ -based visible detectors and GaN-based UV detectors. <i>Photonics Research</i> , 2019 , 7, 1127	6	25
91	Anomalously enhanced thermal stability of phosphorene via metal adatom doping: An experimental and first-principles study. <i>Nano Research</i> , 2016 , 9, 2687-2695	10	25
90	Hardware Implementation of Neuromorphic Computing Using Large-Scale Memristor Crossbar Arrays. <i>Advanced Intelligent Systems</i> , 2021 , 3, 2000137	6	25
89	Electron-beam-irradiated rhenium disulfide memristors with low variability for neuromorphic computing. <i>Npj 2D Materials and Applications</i> , 2021 , 5,	8.8	24
88	Strained n -MOSFET With Embedded Source/Drain Stressors and Strain-Transfer Structure (STS) for Enhanced Transistor Performance. <i>IEEE Transactions on Electron Devices</i> , 2008 , 55, 850-857	2.9	23
87	Self-Selective Multi-Terminal Memtransistor Crossbar Array for In-Memory Computing. <i>ACS Nano</i> , 2021 , 15, 1764-1774	16.7	23

86	Novel NiGe MSM Photodetector Featuring Asymmetrical Schottky Barriers Using Sulfur Co-Implantation and Segregation. <i>IEEE Electron Device Letters</i> , 2008 , 29, 708-710	4.4	21
85	Band alignment of HfO ₂ /multilayer MoS ₂ interface determined by x-ray photoelectron spectroscopy: Effect of CHF ₃ treatment. <i>Applied Physics Letters</i> , 2015 , 107, 101601	3.4	20
84	Recent Advances in Black Phosphorus-Based Electronic Devices. <i>Advanced Electronic Materials</i> , 2019 , 5, 1800666	6.4	20
83	An Electronic Synapse Based on 2D Ferroelectric CuInP ₂ S ₆ . <i>Advanced Electronic Materials</i> , 2020 , 6, 2000760	7.4	19
82	Nearly lattice-matched molybdenum disulfide/gallium nitride heterostructure enabling high-performance phototransistors. <i>Photonics Research</i> , 2019 , 7, 311	6	19
81	Gigahertz Integrated Circuits Based on Complementary Black Phosphorus Transistors. <i>Advanced Electronic Materials</i> , 2018 , 4, 1800274	6.4	19
80	Tunable black phosphorus heterojunction transistors for multifunctional optoelectronics. <i>Nanoscale</i> , 2018 , 10, 14359-14367	7.7	19
79	Effects of Al ₂ O ₃ capping layers on the thermal properties of thin black phosphorus. <i>Applied Physics Letters</i> , 2016 , 109, 261901	3.4	18
78	Low temperature carrier transport study of monolayer MoS ₂ field effect transistors prepared by chemical vapor deposition under an atmospheric pressure. <i>Journal of Applied Physics</i> , 2015 , 118, 124506	2.5	17
77	Enhanced Strain Effects in 25-nm Gate-Length Thin-Body nMOSFETs With Silicon-Carbon Source/Drain and Tensile-Stress Liner. <i>IEEE Electron Device Letters</i> , 2007 , 28, 301-304	4.4	17
76	Pronounced Photovoltaic Effect in Electrically Tunable Lateral Black-Phosphorus Heterojunction Diode. <i>Advanced Electronic Materials</i> , 2018 , 4, 1700442	6.4	17
75	Fabry-Perot cavity enhanced light-matter interactions in two-dimensional van der Waals heterostructure. <i>Nano Energy</i> , 2019 , 62, 667-673	17.1	16
74	Impact of Fin Doping and Gate Stack on FinFET (110) and (100) Electron and Hole Mobilities. <i>IEEE Electron Device Letters</i> , 2012 , 33, 351-353	4.4	16
73	Waveguided Ge/Si Avalanche Photodiode With Separate Vertical SEG-Ge Absorption, Lateral Si Charge, and Multiplication Configuration. <i>IEEE Electron Device Letters</i> , 2009 , 30, 934-936	4.4	16
72	AlGaN/GaN high electron mobility transistors with a low sub-threshold swing on free-standing GaN wafer. <i>AIP Advances</i> , 2017 , 7, 095305	1.5	15
71	Band alignment of atomic layer deposited high-k Al ₂ O ₃ /multilayer MoS ₂ interface determined by X-ray photoelectron spectroscopy. <i>Journal of Alloys and Compounds</i> , 2015 , 650, 502-507	5.7	13
70	Ultrasensitive and robust two-dimensional indium selenide flexible electronics and sensors for human motion detection. <i>Nano Energy</i> , 2020 , 76, 105020	17.1	13
69	Silicon-Carbon Stressors With High Substitutional Carbon Concentration and In Situ Doping Formed in Source/Drain Extensions of n-Channel Transistors. <i>IEEE Electron Device Letters</i> , 2008 , 29, 460-463	4.4	13

68	Strained Thin-Body p-MOSFET With Condensed Silicon-Germanium Source/Drain for Enhanced Drive Current Performance. <i>IEEE Electron Device Letters</i> , 2007 , 28, 509-512	4.4	13
67	Large-Scale Transparent Molybdenum Disulfide Plasmonic Photodetector Using Split Bull Eye Structure. <i>Advanced Optical Materials</i> , 2018 , 6, 1800461	8.1	12
66	Novel Nickel Silicide Contact Technology Using Selenium Segregation for SOI N-FETs With Silicon-Carbon Source/Drain Stressors. <i>IEEE Electron Device Letters</i> , 2008 , 29, 841-844	4.4	12
65	Enhanced performance in 50 nm N-MOSFETs with silicon-carbon source/drain regions		11
64	A unified surface potential based physical compact model for both unipolar and ambipolar 2D-FET: Experimental verification and circuit demonstration 2017 ,		10
63	(Invited) Silicon Photonics Technologies for Monolithic Electronic-Photonic Integrated Circuit. <i>ECS Transactions</i> , 2010 , 28, 3-11	1	10
62	Thermal annealing study of the mid-infrared aluminum nitride on insulator (AlNOI) photonics platform. <i>Optics Express</i> , 2019 , 27, 19815-19826	3.3	10
61	Complementary Black Phosphorus Nanoribbons Field-Effect Transistors and Circuits. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 4122-4128	2.9	10
60	Band alignment of atomic layer deposited TiO ₂ /multilayer MoS ₂ interface determined by x-ray photoelectron spectroscopy. <i>Journal of Alloys and Compounds</i> , 2017 , 698, 141-146	5.7	9
59	Thermal effects on the Raman phonon of few-layer phosphorene. <i>APL Materials</i> , 2015 , 3, 126104	5.7	9
58	Second-order surface-plasmon assisted responsivity enhancement in germanium nano-photodetectors with bull's eye antennas. <i>Optics Express</i> , 2014 , 22, 15949-56	3.3	9
57	Suspended MoS Photodetector Using Patterned Sapphire Substrate. <i>Small</i> , 2021 , 17, e2100246	11	9
56	Laser Annealing of Amorphous Germanium on Silicon-Germanium Source/Drain for Strain and Performance Enhancement in pMOSFETs. <i>IEEE Electron Device Letters</i> , 2008 , 29, 885-888	4.4	8
55	Black phosphorus photonics toward on-chip applications. <i>Applied Physics Reviews</i> , 2020 , 7, 031302	17.3	8
54	Towards low-loss waveguides in SOI and Ge-on-SOI for mid-IR sensing. <i>Journal of Physics Communications</i> , 2018 , 2, 045029	1.2	7
53	Volatile Organic Compound Sensors Based on 2D Materials. <i>Advanced Electronic Materials</i> , 2021 , 7, 2001671	4.1	7
52	Band alignment of ZnO/multilayer MoS ₂ interface determined by x-ray photoelectron spectroscopy. <i>Applied Physics Letters</i> , 2016 , 109, 071602	3.4	7
51	Black phosphorus transistors with enhanced hole transport and subthreshold swing using ultra-thin HfO ₂ high-k gate dielectric 2016 ,		7

50	Unipolar n-Type Conduction in Black Phosphorus Induced by Atomic Layer Deposited MgO. <i>IEEE Electron Device Letters</i> , 2019 , 40, 471-474	4.4	6
49	A flexible InGaAs nanomembrane PhotoFET with tunable responsivities in near- and short-wave IR region for lightweight imaging applications. <i>APL Materials</i> , 2019 , 7, 031503	5.7	6
48	Contact Resistance Reduction Technology Using Selenium Segregation for N-MOSFETs With Silicon-Carbon Source/Drain. <i>IEEE Transactions on Electron Devices</i> , 2009 , 56, 1128-1134	2.9	6
47	Beneath-The-Channel Strain-Transfer-Structure (STS) and Embedded Source/Drain Stressors for Strain and Performance Enhancement of Nanoscale MOSFETs 2007 ,		6
46	Carrier Backscattering Characteristics of Strained N-MOSFET Featuring Silicon-Carbon Source/Drain Regions. <i>Solid-State Device Research Conference, 2008 ESSDERC 2008 38th European</i> , 2006 ,		6
45	In-memory computing using memristor arrays with ultrathin 2D PdSeO /PdSe heterostructure.. <i>Advanced Materials</i> , 2022 , e2201488	24	6
44	First Demonstration of a Fully-Printed Mos2Rram on Flexible Substrate with Ultra-Low Switching Voltage and its Application as Electronic Synapse 2019 ,		5
43	. <i>IEEE Electron Device Letters</i> , 2012 , 33, 631-633	4.4	5
42	Carrier backscattering characteristics of strained silicon-on-insulator n-MOSFETs featuring silicon-carbon source/drain regions. <i>Solid-State Electronics</i> , 2007 , 51, 1444-1449	1.7	5
41	Recent progress on 2D materials-based artificial synapses. <i>Critical Reviews in Solid State and Materials Sciences</i> ,1-26	10.1	5
40	Propagation Loss Improvement in Ge-on-SOI Mid-Infrared Waveguides Using Rapid Thermal Annealing. <i>IEEE Photonics Technology Letters</i> , 2016 , 28, 2447-2450	2.2	5
39	High temperature study on the thermal properties of few-layer Mo0.5W0.5S2 and effects of capping layers. <i>Results in Physics</i> , 2017 , 7, 4394-4397	3.7	4
38	Transition from trap-mediated to band-like transport in polycrystalline monolayer molybdenum disulfide memtransistors. <i>Applied Physics Letters</i> , 2020 , 117, 223101	3.4	4
37	A surface potential based compact model for two-dimensional field effect transistors with disorders induced transition behaviors. <i>Journal of Applied Physics</i> , 2018 , 124, 034302	2.5	3
36	80 GHz bandwidth-gain-product Ge/Si avalanche photodetector by selective Ge growth 2009 ,		3
35	Thin body silicon-on-insulator N-MOSFET with silicon-carbon source/drain regions for performance enhancement		
34	Black Phosphorus Based Photodetectors. <i>ACS Symposium Series</i> , 2019 , 135-153	0.4	3
33	Gate-Defined Quantum Confinement in CVD 2D WS. <i>Advanced Materials</i> , 2021 , e2103907	24	3

32	Interface Modulated Resistive Switching in Mo-irradiated ReS ₂ for Neuromorphic Computing. <i>Advanced Materials</i> , 2020, 32, 202722	24	3
31	A Compact Model for 2-D Poly-MoS ₂ FETs With Resistive Switching in Postsynaptic Simulation. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 4092-4100	2.9	2
30	(Invited) Electrical Characterization and Reliability Assessment of Double-Gate FinFETs. <i>ECS Transactions</i> , 2013 , 50, 201-206	1	2
29	Waveguide-Integrated Ge/Si Avalanche Photodetector with 105GHz Gain-Bandwidth Product 2010 ,		2
28	Nanometer germanium photodetector with aluminum surface plasmon antenna for enhanced photo-response 2010 ,		2
27	Characterization of Strain-Engineered Si:C Epitaxial Layers on Si Substrates. <i>ECS Transactions</i> , 2012 , 45, 23-29	1	2
26	Monolithic Silicon Photonic DWDM Receiver for Terabit Data Communications 2010 ,		2
25	Hot Carrier Reliability of Strained N-Mosfet with Lattice Mismatched Source/Drain Stressors 2007 ,		2
24	Process-Induced Strained P-MOSFET Featuring Nickel-Platinum Silicided Source/Drain. <i>Materials Research Society Symposia Proceedings</i> , 2006 , 913, 1		2
23	Strain-Transfer Structure Beneath the Transistor Channel for Increasing the Strain Effects of Lattice-Mismatched Source and Drain Stressors. <i>Materials Research Society Symposia Proceedings</i> , 2007 , 995, 1		2
22	Towards Low-loss Mid-infrared Waveguides in Ge-on-SOI 2016 ,		2
21	Recent advances in black phosphorus and transition metal dichalcogenideBased electronic and optoelectronics devices 2020 , 251-312		2
20	Nickel-phosphide contact for effective Schottky barrier modulation in black phosphorus p-channel transistors 2016 ,		2
19	Ultrasensitive Flexible Strain Sensor based on Two-Dimensional InSe for Human Motion Surveillance 2019 ,		2
18	Next generation field-effect transistors based on 2D black phosphorus crystal 2015 ,		1
17	Beta-Ga ₂ O ₃ MOSFET Device Optimization via TCAD 2020 ,		1
16	Mid-infrared waveguides in Ge-on-SOI 2016 ,		1
15	Surface-Enhanced Infrared Absorption-Based CO ₂ Sensor using Photonic Crystal Slab 2019 ,		1

14	A new source/drain germanium-enrichment process comprising Ge deposition and laser-induced local melting and recrystallization for P-FET performance enhancement 2008 ,		1
13	Integrated process of photoresist trimming and dielectric hard mask etching for sub-50 nm gate patterning. <i>Thin Solid Films</i> , 2006 , 504, 117-120	2.2	1
12	Hot-Carrier Effects in Strained n-Channel Transistor With Silicon-Carbon $\text{Si}_{1-y}\text{C}_y$ Source/Drain Stressors and Its Orientation Dependence. <i>IEEE Electron Device Letters</i> , 2007 , 28, 996-999	4.4	1
11	Two-dimensional materials toward future photovoltaic devices 2020 , 117-158		1
10	First Demonstration of Waveguide-Integrated Black Phosphorus Electro-Optic Modulator for Mid-Infrared Beyond 4 μm 2019 ,		1
9	A Surface Potential- and Physics- Based Compact Model for 2D Polycrystalline-MoS ₂ FET with Resistive Switching Behavior in Neuromorphic Computing 2018 ,		1
8	A Near- & Short-Wave IR Tunable InGaAs Nanomembrane PhotoFET on Flexible Substrate for Lightweight and Wide-Angle Imaging Applications 2018 ,		1
7	Integration of 2D Black Phosphorus Phototransistor and Silicon Photonics Waveguide System Towards Mid-Infrared On-Chip Sensing Applications 2018 ,		1
6	Ferroelectric memory based on two-dimensional materials for neuromorphic computing. <i>Neuromorphic Computing and Engineering</i> , 2022 , 2, 022001		1
5	Temperature-stable black phosphorus field-effect transistors through effective phonon scattering suppression on atomic layer deposited aluminum nitride. <i>Nanophotonics</i> , 2020 , 9, 2053-2062	6.3	0
4	Mid-infrared modulators integrating silicon and black phosphorus photonics. <i>Materials Today Advances</i> , 2021 , 12, 100170	7.4	0
3	Material and Electrical Characterization of Nickel Silicide-Carbon as Contact Metal to Silicon-Carbon Source and Drain Stressors. <i>Materials Research Society Symposia Proceedings</i> , 2007 , 995, 1		
2	TMD-Based Phototransistors: Anomalous Broadband Spectrum Photodetection in 2D Rhenium Disulfide Transistor (Advanced Optical Materials 23/2019). <i>Advanced Optical Materials</i> , 2019 , 7, 1970088 ^{8.1}		
1	Charge Carrier Mobility and Series Resistance Extraction in 2D Field-Effect Transistors: Toward the Universal Technique. <i>Advanced Functional Materials</i> , 2021 , 31, 2105003	15.6	